

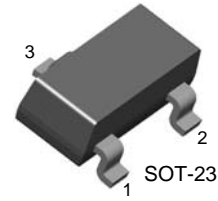


ON Semiconductor®

# BC846 / BC847 / BC848 / BC850 NPN Epitaxial Silicon Transistor

## Features

- Switching and Amplifier Applications
- Suitable for Automatic Insertion in Thick and Thin-film Circuits
- Low Noise: BC850
- Complement to BC856, BC857, BC858, BC859, and BC860



1. Base 2. Emitter 3. Collector

## Ordering Information<sup>(1)</sup>

Part Number	Marking	Package	Packing Method
BC846AMTF	8AA	SOT-23 3L	Tape and Reel
BC846BMTF	8AB	SOT-23 3L	Tape and Reel
BC846CMTF	8AC	SOT-23 3L	Tape and Reel
BC847AMTF	8BA	SOT-23 3L	Tape and Reel
BC847BMTF	8BB	SOT-23 3L	Tape and Reel
BC847CMTF	8BC	SOT-23 3L	Tape and Reel
BC848BMTF	8CB	SOT-23 3L	Tape and Reel
BC848CMTF	8CC	SOT-23 3L	Tape and Reel
BC850AMTF	8EA	SOT-23 3L	Tape and Reel
BC850CMTF	8EC	SOT-23 3L	Tape and Reel

### Note:

1. Affix "-A,-B,-C" means  $h_{FE}$  classification. Affix "-M" means SOT-23 package. Affix "-TF" means the tape and reel type packing.

## Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at  $T_A = 25^\circ\text{C}$  unless otherwise noted.

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	BC846	80
		BC847 / BC850	50
		BC848	30
$V_{CEO}$	Collector-Emitter Voltage	BC846	65
		BC847 / BC850	45
		BC848	30
$V_{EBO}$	Emitter-Base Voltage	BC846 / BC847	6
		BC848 / BC850	5
$I_C$	Collector Current (DC)	100	mA
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	-65 to +150	$^\circ\text{C}$

## Thermal Characteristics<sup>(2)</sup>

Values are at  $T_A = 25^\circ\text{C}$  unless otherwise noted.

Symbol	Parameter	Value	Unit
$P_D$	Power Dissipation	310	mW
	Derate Above $25^\circ\text{C}$	2.48	mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	403	$^\circ\text{C}/\text{W}$

### Note:

2. PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

**Electrical Characteristics<sup>(3)</sup>**Values are at  $T_A = 25^\circ\text{C}$  unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit	
$I_{CBO}$	Collector Cut-Off Current	$V_{CB} = 30\text{ V}, I_E = 0$			15	nA	
$h_{FE}$	DC Current Gain	$V_{CE} = 5\text{ V}, I_C = 2\text{ mA}$	110		800		
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 10\text{ mA}, I_B = 0.5\text{ mA}$		90	250	mV	
		$I_C = 100\text{ mA}, I_B = 5\text{ mA}$		200	600		
$V_{BE(sat)}$	Collector-Base Saturation Voltage	$I_C = 10\text{ mA}, I_B = 0.5\text{ mA}$		700		mV	
		$I_C = 100\text{ mA}, I_B = 5\text{ mA}$		900			
$V_{BE(on)}$	Base-Emitter On Voltage	$V_{CE} = 5\text{ V}, I_C = 2\text{ mA}$	580	660	700	mV	
		$V_{CE} = 5\text{ V}, I_C = 10\text{ mA}$			720		
$f_T$	Current Gain Bandwidth Product	$V_{CE} = 5\text{ V}, I_C = 10\text{ mA},$ $f = 100\text{ MHz}$		300		MHz	
$C_{ob}$	Output Capacitance	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$		3.5	6.0	pF	
$C_{ib}$	Input Capacitance	$V_{EB} = 0.5\text{ V}, I_C = 0, f = 1\text{ MHz}$		9		pF	
NF	Noise Figure	BC846 / BC847 / BC848	$V_{CE} = 5\text{ V}, I_C = 200\text{ }\mu\text{A},$ $R_G = 2\text{ k}\Omega, f = 1\text{ kHz}$		2.0	10.0	dB
		BC850			1.2	4.0	
		BC850		$V_{CE} = 5\text{ V}, I_C = 200\text{ }\mu\text{A},$ $R_G = 2\text{ k}\Omega, f = 30\text{ to }15000\text{ Hz}$		1.4	

**Note:**3. Pulse test: pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$  **$h_{FE}$  Classification**

Classification	A	B	C
$h_{FE}$	110 ~ 220	200 ~ 450	420 ~ 800

## Typical Performance Characteristics

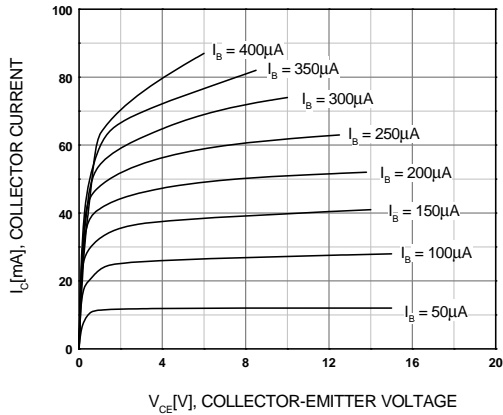


Figure 1. Static Characteristic

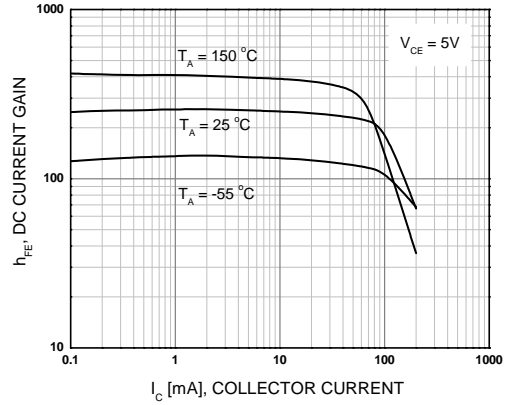


Figure 2. DC Current Gain

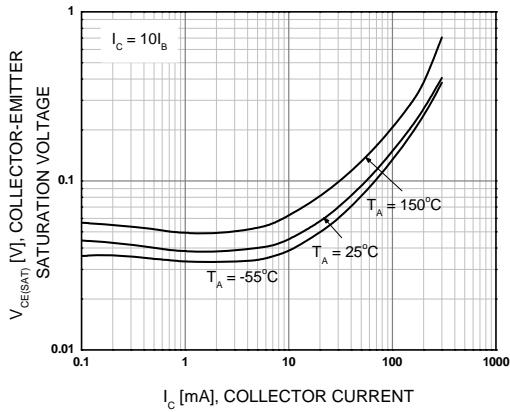


Figure 3. Collector-Emitter Saturation Voltage

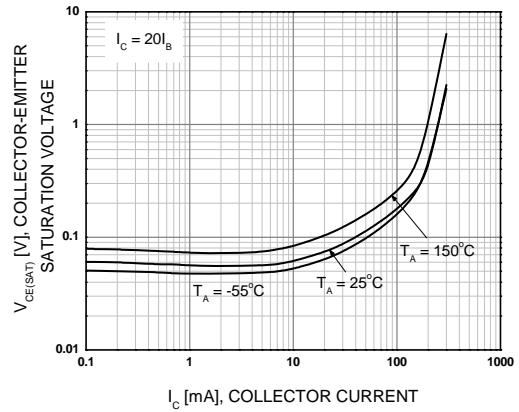


Figure 4. Collector-Emitter Saturation Voltage

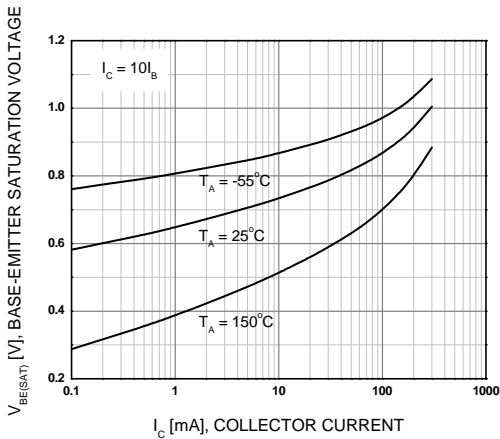


Figure 5. Base-Emitter Saturation Voltage

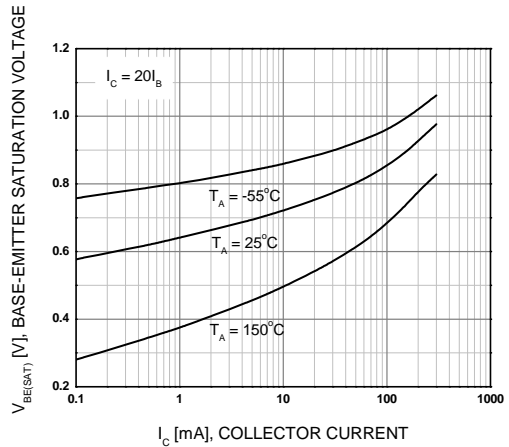


Figure 6. Base-Emitter Saturation Voltage

Typical Performance Characteristics (Continued)

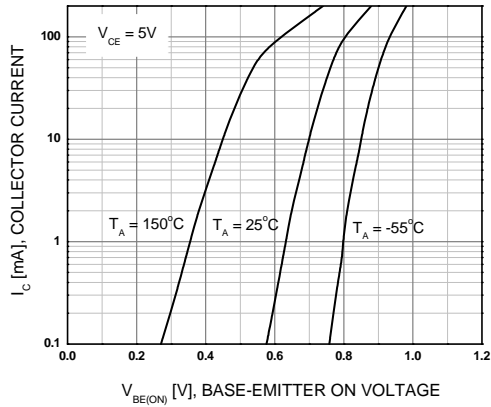


Figure 7. Base-Emitter On Voltage

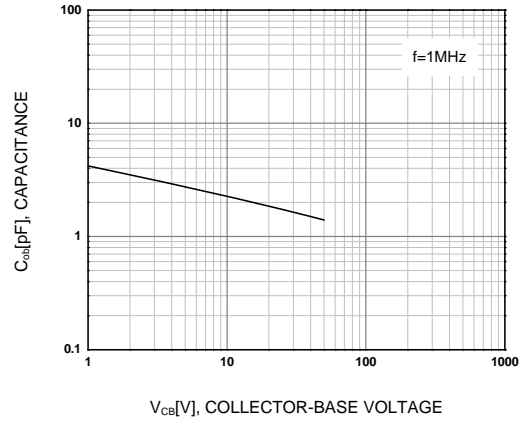


Figure 8. Collector Output Capacitance

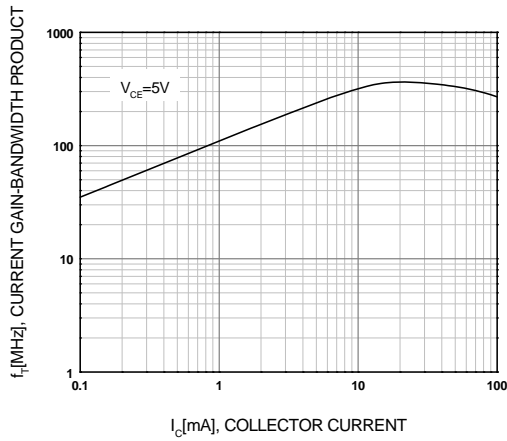


Figure 9. Current Gain Bandwidth Product

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## PUBLICATION ORDERING INFORMATION

### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor  
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA  
**Phone:** 303-675-2175 or 800-344-3860 Toll Free USA/Canada  
**Fax:** 303-675-2176 or 800-344-3867 Toll Free USA/Canada  
**Email:** [orderlit@onsemi.com](mailto:orderlit@onsemi.com)

**N. American Technical Support:** 800-282-9855 Toll Free  
USA/Canada  
**Europe, Middle East and Africa Technical Support:**  
Phone: 421 33 790 2910  
**Japan Customer Focus Center**  
Phone: 81-3-5817-1050

**ON Semiconductor Website:** [www.onsemi.com](http://www.onsemi.com)  
**Order Literature:** <http://www.onsemi.com/orderlit>  
For additional information, please contact your local  
Sales Representative